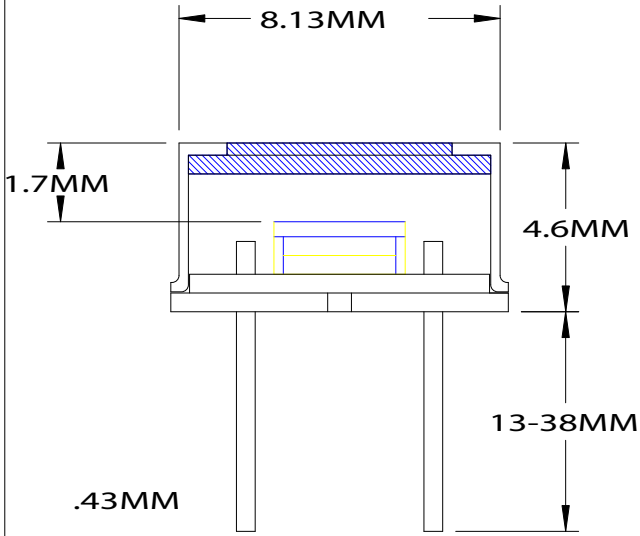


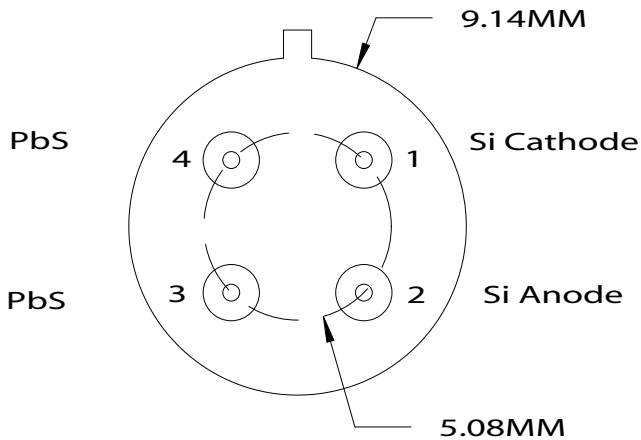
Si SPECIFICATIONS

TOP Si PV PHOTODIODE
 ACTIVE AREA - 3.5MM Dia
 WAVELENGTH - .3-1.1u
 SHUNT RESISTANCE - 1500M @10mV
 DARK CURRENT - 0.2nA @10V
 CAPACITANCE - 100pF @0V
 RESPONSIVITY - .65A/W @900nm
 NEP(W/Hz)-1.3×10^{-14} @900nm
 TIME CONSTANT - 2000ns @0V



PbS SPECIFICATIONS

BOTTOM PbS PC DETECTOR
 ACTIVE AREA - 3MMX3MM
 WAVELENGTH - 1.0 - 3.0u
 RESISTANCE - 0.3 - 2.0 M ohms
 RESPONSIVITY - >math>6 \times 10^4</math> V/W
 $D^*(Pk,600,1) \times 10^{10} - 5.0$ Min
 TIME CONSTANT - 200-400usec



NOTE:

- All assemblies are hermetically sealed
- Custom filters are available
- Other active areas are available
- PbSe and InGaAs materials are available

DO NOT SCALE DRAWING	DRAWN		DATE	N.E.P. NEW ENGLAND PHOTOCONDUCTOR				
	CHECKED		DATE					
	DESIGNER	GG	DATE	BS-2/2.5-5				
	ENGINEER	PB	DATE					
MATERIAL:	PROJECT ENGINEER		DATE	SIZE	CODE IDENT. NO.	TYPE	1643	REV
FINISH SPECS:	PROJECT APPROVAL		DATE	A				
PMB 3/3/09				SCALE none			1	SHEET
SUNSTAR传感与控制 http://www.sensor-ic.com/ TEL:0755-83376549 FAX:0755-83376182 E-MAIL:szss20@163.com								